

## BC214LC

# **PNP General Purpose Amplifier**

- This device is deisgned for use as general purpose amplifiers and switches requiring collector currents to 300mA.
- Sourced from process 68.



1. Emitter 2. Collector 3. Base

## **Absolute Maximum Ratings\*** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	-30	V
V <sub>CBO</sub>	Collector-Base Voltage	-45	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5.0	V
I <sub>C</sub>	Collector Current (DC) Continuous	-500	mA
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- These ratings are based on a maximum junction temperature of 150 degrees C.
   These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

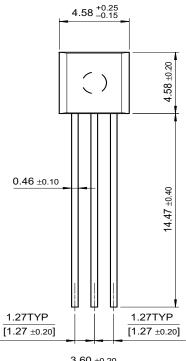
## **Electrical Characteristics** T<sub>a</sub>=25°C unless otherwise noted

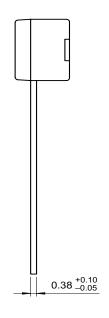
Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characte	eristics	•		•	•
V <sub>(BR)CEO</sub>	Collector-Emitter Voltage	I <sub>C</sub> = -2mA, I <sub>B</sub> = 0	-30		V
V <sub>(BR)CBO</sub>	Collector-Base Voltage	$I_{C} = -10\mu A, I_{E} = 0$	-45		V
V <sub>(BR)EBO</sub>	Emitter-Base Voltage	$I_E = -10\mu A, I_C = 0$	-5.0		V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = -30V, I_{E} = 0$		-15	nA
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = -4V, I <sub>C</sub> = 0		-15	nA
On Characte	eristics *	•		•	•
h <sub>FE</sub>	DC Current Gain	$V_{CE} = -5V, I_{C} = -2mA$	140	400	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA I <sub>C</sub> = -100mA, I <sub>B</sub> = -5mA		-0.25 -0.6	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = -100mA, I <sub>B</sub> = -5mA		-1.1	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> = -5V, I <sub>C</sub> = -2mA	-0.6	-0.72	V
Small Signa	I Characteristics		· ·		
f <sub>T</sub>	Current gain Bandwidth Product	$V_{CE} = -5V, I_{C} = -10mA$ f = 100MHz	200		MHz
NF	Noise Figure	$V_{CE}$ = -5V, $I_{C}$ = -200μA $R_{G}$ = 2k $\Omega$ , $f$ = 15.7KHz		2.0	dB
h <sub>fe</sub>	Small Signal Current Gain	$I_C = -2mA$ , $V_{CE} = -5V$ f = 1KHz	350	600	
C <sub>OB</sub>	Output Capacitance	V <sub>CB</sub> = -10V, f = 1MHz		10	pF

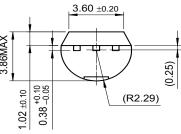
\* Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2.0%

Thermal Characteristics TA=25°C unless otherwise noted			
Symbol	Parameter	Max.	Units
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{ heta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

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